

HD74ALVCH16820

3.3-V 10-bit Flip Flops with Dual Outputs

REJ03D0034-0400Z (Previous ADE-205-170B(Z)) Rev.4.00 Oct.02.2003

Description

The flip flops of the HD74ALVCH16820 are edge triggered D-type flip flops. On the positive transition of the clock (CLK) input, the device provides true data at the Q outputs. A buffered output enable (\overline{OE}) input can be used to place the ten outputs in either a normal logic state (high or low logic level) or a high impedance state. In the high impedance state, the outputs neither load nor drive the bus lines significantly. The high impedance state and increased drive provide the capability to drive bus lines without need for interface or pullup components. \overline{OE} input does not affect the internal operation of the flip flops. Old data can be retained or new data can be entered while the outputs are in the high impedance state. Active bus hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

Features

- $V_{CC} = 2.3 \text{ V to } 3.6 \text{ V}$
- Typical V_{OL} ground bounce < 0.8 V (@ V_{CC} = 3.3 V, Ta = 25°C)
- Typical V_{OH} undershoot > 2.0 V (@ V_{CC} = 3.3 V, T_a = 25°C)
- High output current ± 24 mA (@V_{CC} = 3.0 V)
- Bus hold on data inputs eliminates the need for external pullup / pulldown resistors

Function Table

Inputs OEn *2		Output Qn *1		
OEn *2	CLK	D		
L	↑	Н	Н	
L	↑	L	L	
L	L	Х	Q ₀ *1	
Н	Х	X	Z	

H: High level

L : Low level

X: Immaterial

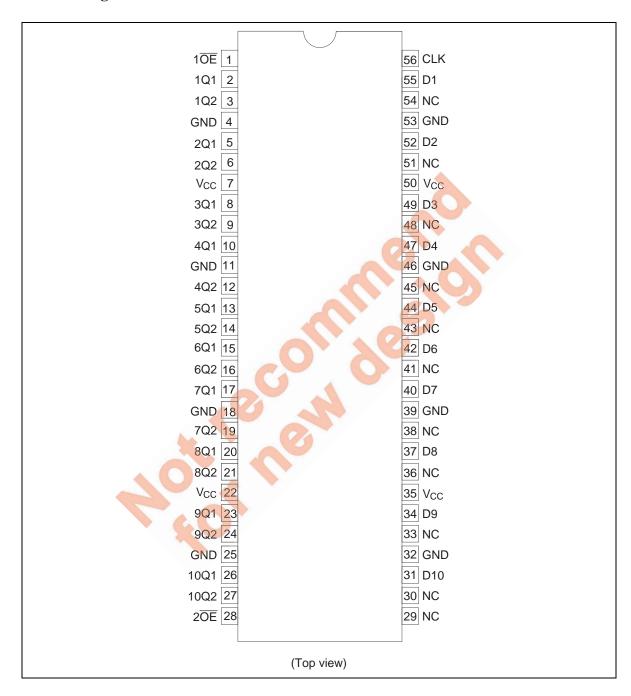
Z: High impedance

↑: Low to high transition

Notes: 1. Output level before the indicated steady state input conditions were established.

2. n = 1, 2

Pin Arrangement



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage	V _{CC}	-0.5 to 4.6	V	
Input voltage *1	Vı	-0.5 to 4.6	V	
Output voltage *1, 2	Vo	-0.5 to V _{CC} +0.5	V	
Input clamp current	I _{IK}	- 50	mA	V _I < 0
Output clamp current	I _{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	I _O	±50	mA	$V_O = 0$ to V_{CC}
V _{CC} , GND current / pin	I _{CC} or I _{GND}	±100	mA	
Maximum power dissipation at Ta = 55°C (in still air) *3	P _T	1	W	TSSOP
Storage temperature	Tstg	-65 to 150	°C	

Notes: Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum rated conditions for extended periods may affect device reliability.

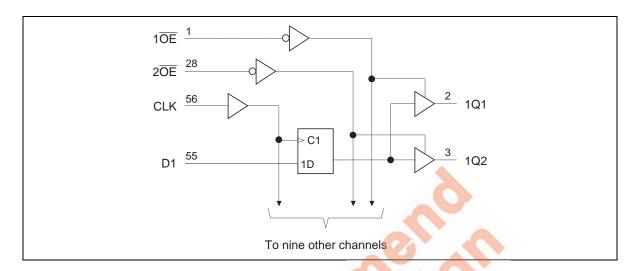
- 1. The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.
- 2. This value is limited to 4.6 V maximum.
- 3. The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils.

Recommended operating conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage	V _{CC}	2.3	3.6	V	
Input voltage	VI	0	V_{CC}	V	
Output voltage	Vo	0	V_{CC}	V	
High level output current	I _{OH}	_	-12	mA	$V_{CC} = 2.3 \text{ V}$
		_	-12		$V_{CC} = 2.7 \text{ V}$
		_	-24		$V_{CC} = 3.0 \text{ V}$
Low level output current	I _{OL}	_	12	mA	$V_{CC} = 2.3 \text{ V}$
		_	12		$V_{CC} = 2.7 \text{ V}$
		_	24		$V_{CC} = 3.0 \text{ V}$
Input transition rise or fall	rate Δt / Δv	0	10	ns / V	
Operating temperature	Та	-40	85	°C	

Note: Unused control inputs must be held high or low to prevent them from floating.

Logic Diagram



Electrical Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

Item	Symbol	V _{CC} (V) *1	Min	Max	Unit	Test Conditions
Input voltage	V _{IH}	2.3 to 2.7	1.7	_	V	
		2.7 to 3.6	2.0	_	_	
	V _{IL}	2.3 to 2.7	_	0.7	_	
		2.7 to 3.6	_	0.8	_	
Output voltage	V _{OH}	Min to Max	V _{CC} -0.2	_	V	$I_{OH} = -100 \mu A$
		2.3	2.0	_	_	$I_{OH} = -6 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.3	1.7	_		$I_{OH} = -12 \text{ mA}, V_{IH} = 1.7 \text{ V}$
		2.7	2.2	_	1	$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.4	- //		$I_{OH} = -12 \text{ mA}, V_{IH} = 2.0 \text{ V}$
		3.0	2.0	- ~	9	$I_{OH} = -24 \text{ mA}, V_{IH} = 2.0 \text{ V}$
	V _{OL}	Min to Max	_	0.2		I _{OL} = 100 μA
		2.3	- 4	0.4		$I_{OL} = 6 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.3		0.7	6	$I_{OL} = 12 \text{ mA}, V_{IL} = 0.7 \text{ V}$
		2.7	AT.	0.4	3	$I_{OL} = 12 \text{ mA}, V_{IL} = 0.8 \text{ V}$
		3.0		0.55		$I_{OL} = 24 \text{ mA}, V_{IL} = 0.8 \text{ V}$
Input current	I _{IN}	3.6	- 4	±5	μΑ	$V_{IN} = V_{CC}$ or GND
	I _{IN (hold)}	2.3	45	_	=	$V_{IN} = 0.7 \text{ V}$
		2.3	-45	_	=	V _{IN} = 1.7 V
	*	3.0	75	_	=	V _{IN} = 0.8 V
		3.0	- 75	_	_	V _{IN} = 2.0 V
		3.6		±500	=	V _{IN} = 0 to 3.6 V
Off state output current *2	loz	3.6	_	±10	μΑ	$V_{OUT} = V_{CC}$ or GND
Quiescent supply current	Icc	3.6	_	40	μΑ	$V_{IN} = V_{CC}$ or GND
	ΔI_{CC}	3.0 to 3.6	_	750	μΑ	V_{IN} = one input at (V _{CC} -0.6) V, other inputs at V _{CC} or GND

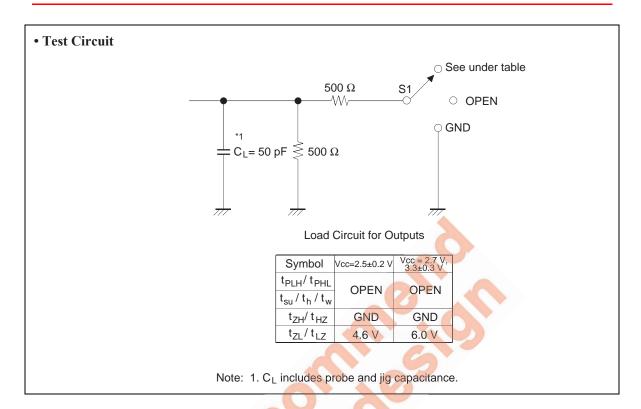
Notes: 1. For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

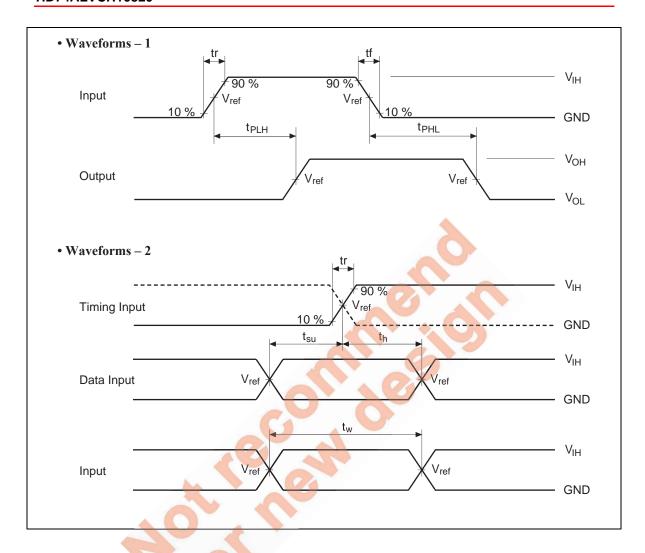
^{2.} For I/O ports, the parameter I_{OZ} includes the input leakage current.

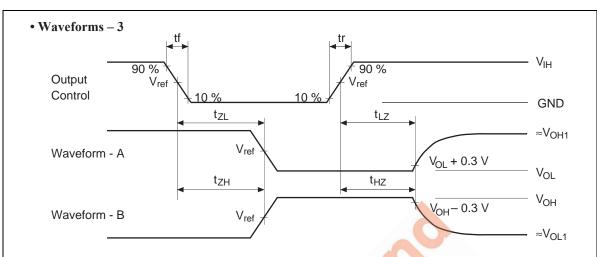
Switching Characteristics

 $(Ta = -40 \text{ to } 85^{\circ}C)$

Item	Symbol	V _{CC} (V)	Min	Тур	Max	Unit	FROM (Input)	TO (Output)
Maximum clock frequency	f_{max}	2.5±0.2	150	_	_	MHz		_
		2.7	150	_	_			
		3.3±0.3	150	_	_			
Propagation delay time	t_{PLH}	2.5±0.2	1.0	_	5.9	ns	CLK	Q
	t_{PHL}	2.7	_	_	5.5			
		3.3 ± 0.3	1.0	_	4.8			
Output enable time	t_{ZH}	2.5±0.2	1.0	_	6.4	ns	ŌĒ	Q
	t_{ZL}	2.7	_	- 4	6.1			
		3.3±0.3	1.0	-	5.0			
Output disable time	t _{HZ}	2.5±0.2	1.3	70	5.7	ns	ŌĒ	Q
	t_{LZ}	2.7		1-02	5.0			
		3.3±0.3	1.0		4.5			
Setup time	t _{su}	2.5±0.2	1.7	-	7	ns		
		2.7	1.8	-//				
		3.3±0.3	1.4		_			
Hold time	t _h	2.5±0.2	1.1	-	_	ns		
	4	2.7	1.1	<u> </u>	_			
	A 7	3.3±0.3	1.0	_	_			
Pulse width	t _w	2.5±0.2	3.3		_	ns		
		2.7	3.3	_	_	_		
		3.3±0.3	3.3		_			
Input capacitance	C _{IN}	3.3	_	3.5	_	pF	Control inp	outs
		3.3	_	6.0	_	_	Data input	S
Output capacitance	Co	3.3	_	7.0	_	pF	Outputs	





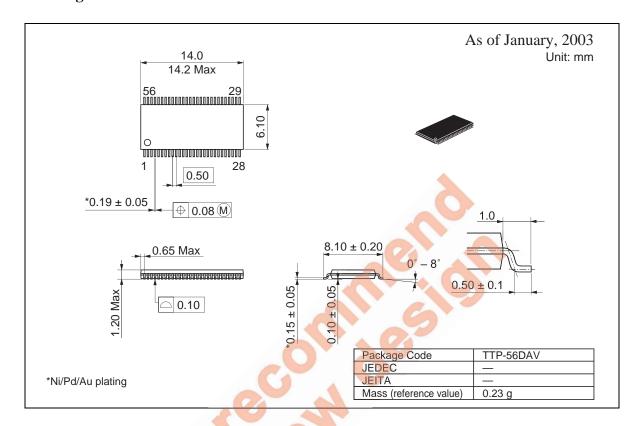


TEST	Vcc=2.5±0.2 V	$Vcc = 2.7 \text{ V}, 3.3\pm0.3 \text{ V}$
V _{IH}	2.3 V	2.7 V
V _{ref}	1.2 V	1.5 V
V _{OH1}	2.3 V	3.0 V
V _{OL1}	GND	GND

Notes: 1. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Zo = 50 Ω , tr \leq 2.5 ns, tf \leq 2.5 ns.

- 2. Waveform A is for an output with internal conditions such that the output is low except when disabled by the output control.
- 3. Waveform B is for an output with internal conditions such that the output is high except when disabled by the output control.
- 4. The output are measured one at a time with one transition per measurement.

Package Dimensions



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